



Hole transfer layer engineering for CdTe nanocrystal photovoltaics with improved efficiency

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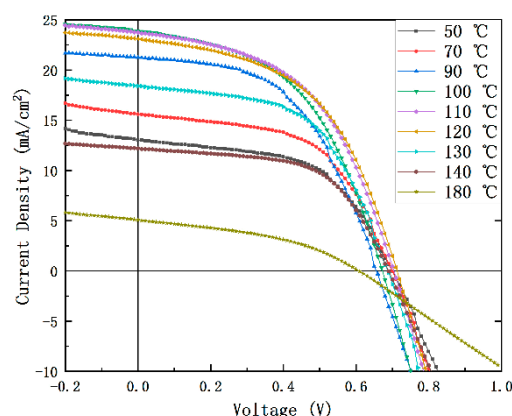


Figure S1. J-V curves of NC solar cells with Spiro HTL annealing at different temperature

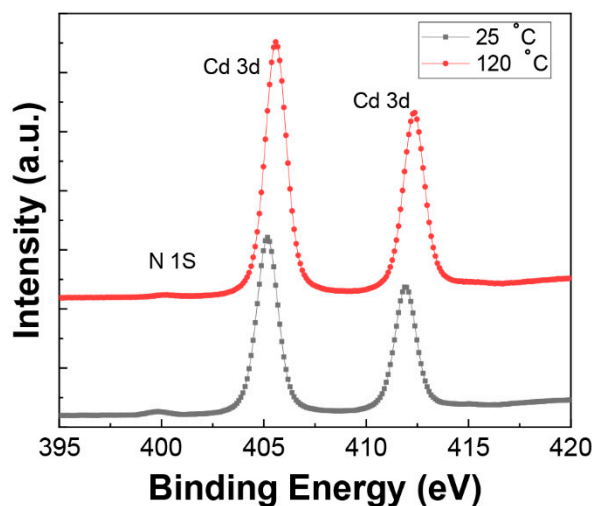


Figure S2. The narrow XPS spectra of Cd3d for ITO/ZnO/CdS/CdSe/CdTe/Spiro with different annealing temperature

Table S1. Summarized XPS values of Cd 3d with HTL annealing at different temperature (Figure S2)

treatment condition	Cd3d5/2	Cd3d3/2
25 °C	405.08	411.88
120 °C	405.38	412.18

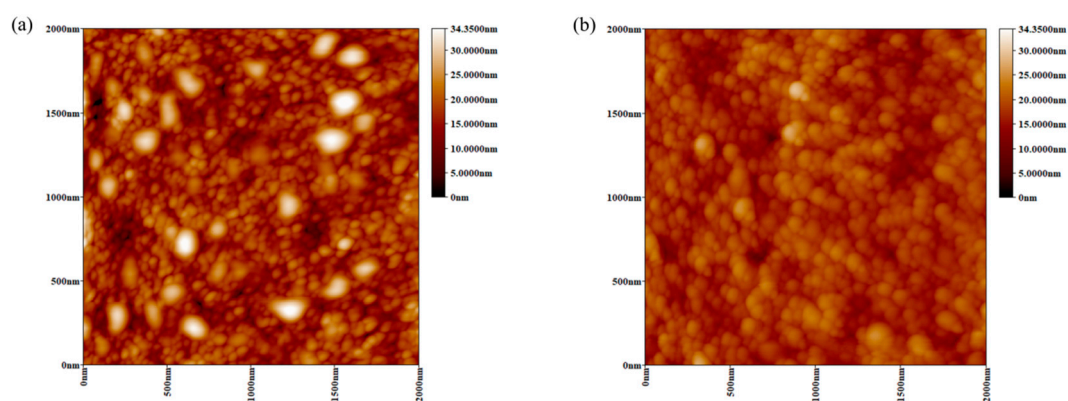


Figure S3. AFM image of HTL (a) without annealing (25°C) and (b) annealing at 120°C